N-Channel Silicon MOSFET



2SK1691

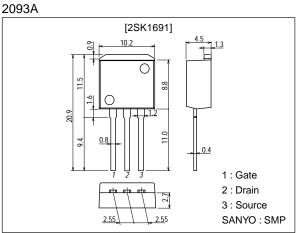
# **Ultrahigh-Speed Switching Applications**

## Features

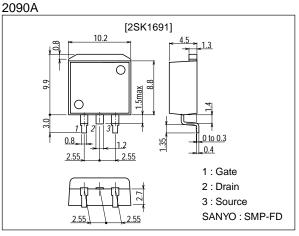
- · Low ON resistance.
- · Ultrahigh-speed switching.

# **Package Dimensions**

unit:mm



## unit:mm



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SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

# **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

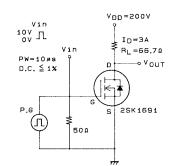
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		450	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	Ι <sub>D</sub>		5	A
Drain Current (pulse)	I <sub>DP</sub>		20	A
Allowable Power Dissipation	PD		1.65	W
		Tc=25°C	60	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

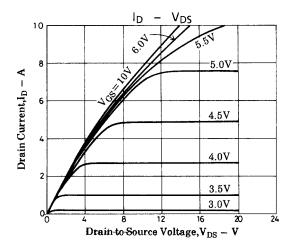
### Electrical Characteristics at Ta = 25°C

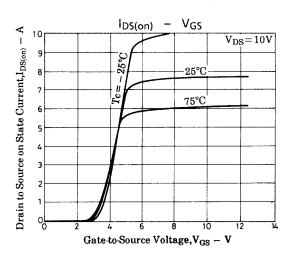
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	450			V
Zero-Gate Votlage Drain Current	IDSS	V <sub>DS</sub> =450V, V <sub>GS</sub> =0			1.0	mA
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±30V, V <sub>DS</sub> =0			±100	nA
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	2.0		3.0	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	2.0	4.0		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =3A, V <sub>GS</sub> =10V		1.0	1.4	Ω
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		700		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		100		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =20V, f=1MHz		40		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit		15		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit		30		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit		130		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit		45		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> =0			1.8	V

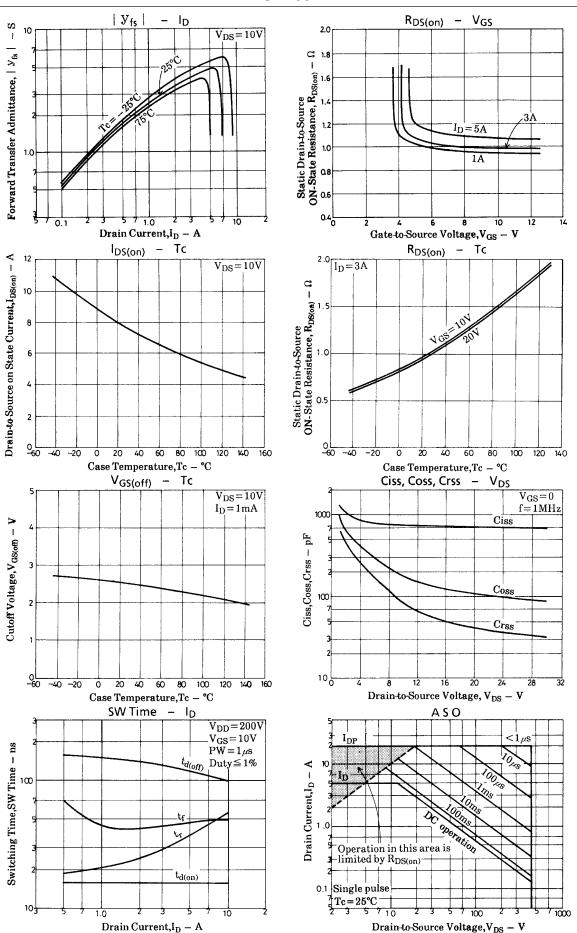
(Note) Be careful in handling the 2SK1691 because it has no protection diode between gate and source.

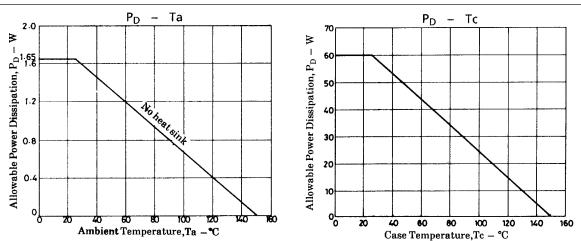
### **Switching Time Test Circuit**











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